Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION *(Use several sheets if necessary)*	Docket Number (Optional) 4308.4US (99-1199.04/US)	Application Number 10/791400
	Applicant **John T. Moore**	
	Filing Date **March 2, 2004**	Group Art Unit 2824

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CDW	5,567,638	10/1996	Lin et al.	438	592	
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	6,013,553	01/2000	Wallace et al.	438	287	
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

CDW		Al-Shareef et al., "Device Performance of *in situ* Steam Generated Gate Dielectric Nitrided by Remote Plasma Nitridation", Applied Physics Letters, Volume 78, Number 24, June 11, 2001, pps. 3875-3877.
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CDW		Hattangady et al., "Ultrathin Nitrogen-Profile Engineered Gate Dielectric Films", IEDM Tech. Dig., 1996, pps. 495-498.

EXAMINER	DATE CONSIDERED
Christian Wilson	9/8/04

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